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Preparation of Cu₂O Films with Preferred Crystal Orientations by Electrodeposition Method†

LING XU¹, CHANG-LING LIU², SHI-BIAO WU^{1,*}, FANG-TAO TAO¹ and SHI-LONG WU¹

¹School of Materials & Chemical Engineering, Anhui Jianzhu University, Hefei 230022, P.R. China

²Hefei Teachers College, Hefei 230061, P.R. China

*Corresponding author: E-mail: wslb@ahjzu.edu.cn

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Cuprous oxide (Cu₂O) films were electrodeposited by potentiostatic method on the indium tin oxide conductive glass substrate. The films were characterized by XRD and SEM. The electrodeposition process conditions for the preparation of Cu₂O films with preferred orientations of (111) or (200) lattice plane were investigated. According to the result of experiments, the preferred crystal orientations of the obtained Cu₂O films were related to electrodeposition potential and the molar ratio of CuSO₄ vs. lactic acid in plating solution.

Keywords: Electrochemistry, Cathodic deposition, Cuprous oxide film, Structure, Appearance.

INTRODUCTION

Cuprous oxide (Cu₂O), is one of the most important semiconductor materials with a narrow band gap ($E_g = 2.17$ eV)¹, widely used as gas sensors, solar cells and photocatalysis². It can be used as the absorption layer material of solar cell that theoretical photoelectric conversion efficiency is as high as 20 %³. In addition, as a effective photocatalyst, the successful application of Cu₂O photodegradation technique to remove methylene blue from dyeing wastewater has been reported⁴. Today, there were many methods to prepare Cu₂O film⁵. Electrodeposition method is a low-temperature and environment-friendly soft chemical method which has many advantages, such as simple preparation process, low cost, high purity and large area thin film products⁴. Furthermore, the structure and thickness of the electrodeposited film are easy to control by adjusting electrodeposition process parameters. Many researches proved the temperature, current density and pH value of plating solution were the process parameters which influence the morphologies and quality of electrodeposited films⁶. However, there were few reports about the effect of electrode potential on preferred crystal orientations of Cu₂O films prepared by electrodeposition method. In this paper, the films with different preferred crystal orientations were electrodeposited by potentiostatic method and proper process parameters, such as electrodeposition potential and the molar ratio of CuSO₄ vs. lactic acid in plating solution would be discussed.

EXPERIMENTAL

All reagents were of analytical grade and used without further purification. The Cu₂O thin films were electrodeposited on commercial indium tin oxide glass (HYSTN80, Huayi Conductive Glass Co. Ltd., Anhui, PRC) substrates in potentiostatic mode. All electrodeposition experiments were carried out by three-electrode cell⁷, using Cu foil (3 cm × 3 cm), indium tin oxide glass substrate (1 cm × 2 cm) and saturated calomel electrode (SCE) as the counter electrode, working electrode and reference electrode, respectively. The cell was powered by a potentiostat (DJS-292, Shanghai REX Instrument Factory, Shanghai, PRC).

Before deposition, the substrate was cleaned by ultrasonic treatment in toluene, acetone and ethanol in turn, rinsed by distilled water and washed with deionized water, then dried in air. Afterward, it was immersed in plating electrolyte. There were two plating solutions, named after 1#, 2# in this paper, containing 0.2 and 0.64 mol/L lactic acid, respectively. Two plating solutions all contained 0.1 mol/L CuSO₄. Therefore, the molar ratio of CuSO₄ vs. lactic acid in 1# and 2# plating solution were 1:2 and 1:6.4, respectively. Before been using, the solutions' pH value was raised to 10 by dropwise adding 15 mol/L NaOH solution, under constant stirring; A pH meter (pHS-2C, Shanghai REX Instrument Factory, Shanghai, PRC) was used as a pH detector.

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Deposition potential was varied in the range -0.4 to -3.0V (*vs.* SCE) and the time of deposition⁴ was 25 min. The electro-deposition temperature was at 75 °C. After deposition, the working electrode with Cu₂O films was taken from the cell and washed with deionized water, then dried in air at room temperature.

The structure and overall crystallinity in Cu₂O films was characterized through θ -2 θ scans operated on a X-ray diffractometer (Y-2000, Dandong radiative instrument group Co. Ltd. Liaoning, PRC) with CuK α radiation ($\lambda = 1.5406 \text{ \AA}$). The surface morphology of the prepared film was investigated through scanning electron microscopy on a field-emission SEM (Sirion200, FEI Company, USA) operated at 5 kV voltage value.

RESULTS AND DISCUSSION

Effect of deposition potential on preferred crystal orientations of Cu₂O films

Cu₂O films deposited in 1# plating solution at different potential series: Fig. 1 shows the X-ray diffraction patterns of the different Cu₂O films electrodeposited at different potential from -0.2 to -2.2 V (*vs.* SCE) in 1# plating solution in which the molar ratio of CuSO₄ *vs.* lactic acid is 1:2. Fig. 1 shows the deposited Cu₂O films are grown along preferred (111) crystal planes when deposition potential is from -0.6 to -2.2 V (*vs.* SCE) and the Cu₂O films is preferred (200) crystal growth when the potential is from -0.2 to -0.4 V (*vs.* SCE). Comparing XRD patterns in Fig. 2, it can be observed that the films prepared with electrode potential of -1.6 V (*vs.* SCE) has the most strong (111) reflection peak than the others. Commonly, the strong reflection peaks imply the good degree of crystallinity⁸. According to the diffraction intensity of (111) plane, the films deposited at -1.6 V (*vs.* SCE) have the best degree of crystallinity and optimal deposition potential is -1.6 V (*vs.* SCE).

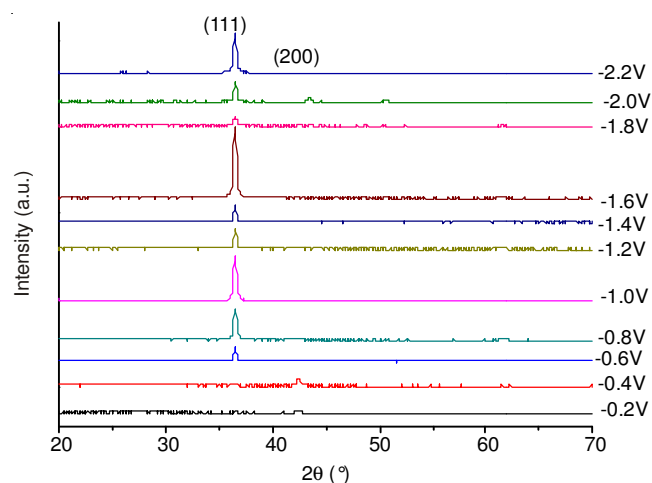


Fig. 1. Effect of potential on preferred crystal orientations of Cu₂O films deposited in 1# plating solution in which the molar ratio of CuSO₄ *vs.* lactic acid is 1:2

Cu₂O films deposited in 2# plating solution at different potential series: Fig. 2 shows the X-ray diffraction patterns of the different Cu₂O films electrodeposited at different deposition

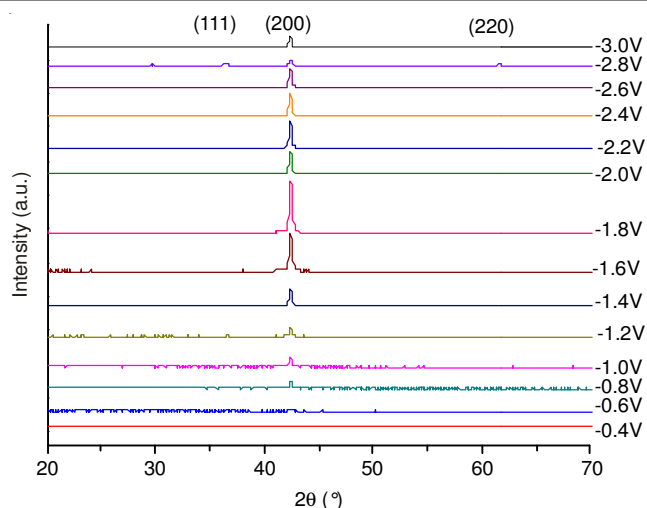
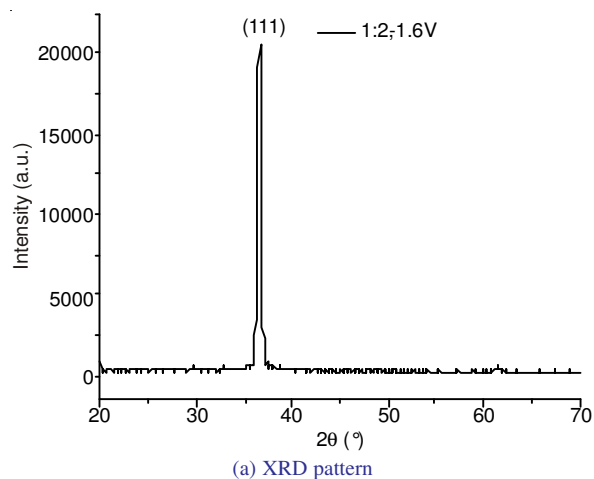


Fig. 2. Effect of potential on preferred crystal orientations of Cu₂O films deposited in 2# plating solution in which the molar ratio of CuSO₄ *vs.* lactic acid is 1:6.4

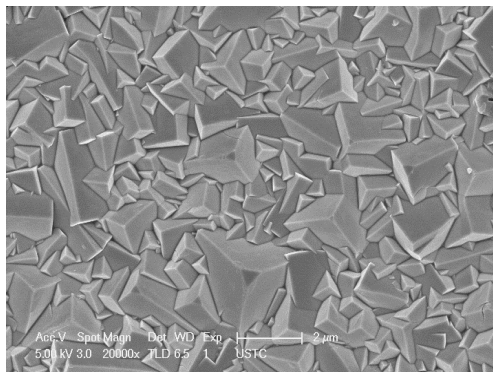
potential from -0.4 to -3.0V (*vs.* SCE) in 2# plating solution in which the molar ratio of CuSO₄ *vs.* lactic acid is 1:6.4. The films have preferred (200) crystal orientation when deposition potential is from -0.6 to -2.6 V (*vs.* SCE). According to the (200) peaks' intensity, the films deposited at -1.8 V (*vs.* SCE) have the best degree of crystallinity and optimal deposition potential is -1.8 V (*vs.* SCE).

Characterization of Cu₂O films prepared at optimal deposition potential: XRD patterns and SEM images of two films prepared at optimal deposition potential are as follows. One film was deposited in 1# plating solution at -1.6V (*vs.* SCE), which has (111) preferred crystal orientation. Another was deposited in 2# plating solution at -1.8V (*vs.* SCE), which has (200) preferred crystal orientation.

Cu₂O film with (111) preferred crystal orientation: Fig. 3 shows the X-ray diffraction pattern and SEM image of the Cu₂O film deposited at -1.6V (*vs.* SCE) in 1# plating solution in which the molar ratio of CuSO₄ *vs.* lactic acid was 1:2. According to Fig. 3(a), peaks on the XRD pattern are accurately accorded with the standard PDF card No. 77-0199 pattern. It is obvious that the film is of cubic lattice system ($a = 4.258 \text{ \AA}$). Fig. 3(b) shows the top-view SEM image of the film. The crystal grains are simple and regular cubic shape and are of high degree of crystallinity.



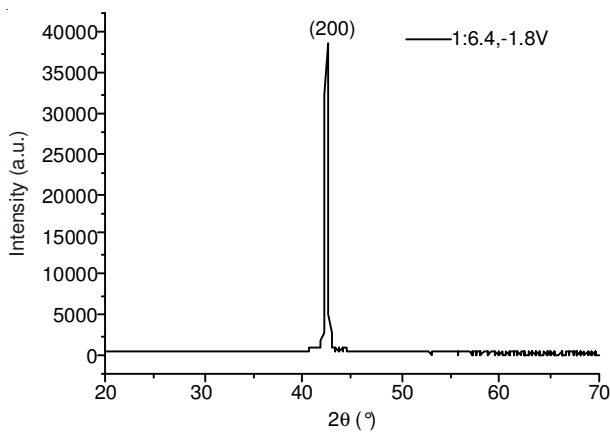
(a) XRD pattern



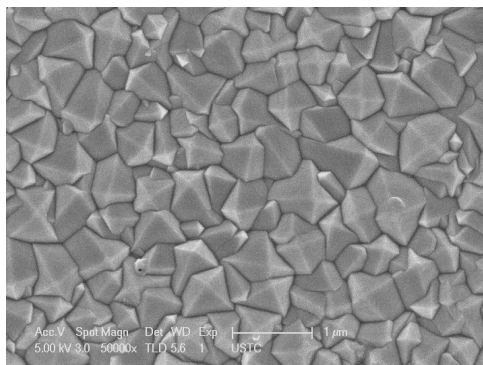
(b) SEM image

Fig. 3. XRD pattern and SEM image of Cu₂O film with (111) preferred crystal orientation

Cu₂O film with (200) preferred crystal orientation: Fig. 4 shows the X-ray diffraction pattern and SEM image of the Cu₂O film deposited at -1.8V (vs. SCE) in 2# plating solution in which the molar ratio of CuSO₄ vs. lactic acid was 1:6.4. According to Fig. 4(a), peaks on the XRD pattern are accurately accorded with the standard PDF card No. 05-0667 pattern. It is obvious that the film is of cubic lattice system ($a = 4.27 \text{ \AA}$). Fig. 4(b) shows the top-view SEM image of the film. The crystal grains are octahedral shape and also have high degree of crystallinity.



(a) XRD pattern



(b) SEM image

Fig. 4. XRD pattern and SEM image of Cu₂O film with (200) preferred crystal orientation

Conclusion

In summary, a low-temperature and environment-friendly soft chemical electrodeposition technique had been successfully applied to fabricate Cu₂O thin films with preferred orientations of (111) or (200) lattice plane. Because of controllability, the potentiostatic mode was applied to deposition process. The time and temperature of deposition process were 25 min and 75 °C, respectively. According to the result of experiments, the films' preferred crystal orientations were related to electrodeposition potential and the molar ratio of CuSO₄ vs. lactic acid in plating solution. Cu₂O thin film with preferred crystal orientation of (111) can be deposited at electrode potential arranging from -0.6 V ~ -2.2 V (vs. SCE) in 1# plating solution in which the molar ratio of CuSO₄ vs. lactic acid was 1:2. Cu₂O thin film with preferred crystal orientation of (200) can be deposited at electrode potential arranging from -0.6 V ~ -2.6 V (vs. SCE) in 2# plating solution in which the molar ratio of CuSO₄ vs. lactic acid was 1:6.4. The deposition potential arrangement of Cu₂O thin film with (200) preferred crystal orientation was wider than the films with (111) preferred crystal orientation.

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